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METHOD FOR FORMING A DIELECTRIC LAYER AND SEMICONDUCTOR DEVICE
INCORPORATING THE SAME

FIELD OF THE INVENTION

5 The present invention relates to the field of semiconductors and, more particularly, to an improved dielectric for increasing semiconductor performance.

CROSS-REFERENCES TO RELATED APPLICATIONS

10 This application is related to commonly assigned U.S. Patent Application Serial Nos.: 09/653,639, METHOD FOR FORMING A BARRIER LAYER TO INCREASE SEMICONDUCTOR DEVICE PERFORMANCE, filed August 31, 2000, by Powell et al. and 09/653,298, METHOD FOR FORMING A DIELECTRIC LAYER AT A LOW TEMPERATURE, filed August 31, 2000, by Mercaldi et al., the disclosures of which are incorporated herein by reference. This application is a divisional of U.S. Patent Application Serial No. 09/653,096, filed August 31, 2000, now Patent No. 6576964.

BACKGROUND OF THE INVENTION

20 There is a constant demand for semiconductor devices of a reduced size. The performance characteristics of semiconductor capacitors, transistors, electrode layers and the like become more critical as device size decreases. Accordingly, processes